

General Description

The 80N70 uses advanced trench technology to provide excellent RDS(ON). These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

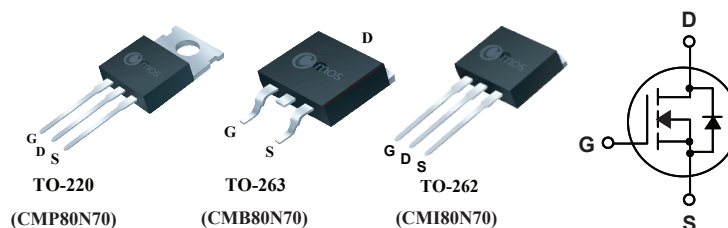
Product Summary

BVDSS	RDS(on) max.	ID
68V	8mΩ	80A

Applications

- Motor Control
- DC-DC converters
- Switching applications

TO-220/263/262 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	68	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current	80	A
I _D @T _C =100°C	Continuous Drain Current	50	A
I _{DM}	Pulsed Drain Current ¹	320	A
EAS	Single Pulse Avalanche Energy ²	520	mJ
P _D @T _C =25°C	Total Power Dissipation	150	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient	---	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case	---	0.83	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	68	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =40A	---	7	8	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2	---	4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	---	---	1	uA
		V _{DS} =60V, V _{GS} =0V, T _J =125°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V	---	---	±100	nA
g _{fs}	Forward Transconductance ³	V _{DS} =10V, I _D =25A	---	18	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.5	---	Ω
Q _g	Total Gate Charge	I _D =80A	---	75	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =37.5V	---	19	---	
Q _{gd}	Gate-Drain Charge	V _{GS} =10V	---	25	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =37.5V	---	25	---	ns
T _r	Rise Time	I _D =39A	---	65	---	
T _{d(off)}	Turn-Off Delay Time	R _G =4.7 Ω	---	90	---	
T _f	Fall Time	V _{GS} =10V	---	45	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	3500	---	pF
C _{oss}	Output Capacitance		---	360	---	
C _{rss}	Reverse Transfer Capacitance		---	290	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	80	A
I _{SM}	Pulsed Source Current ¹		---	---	320	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =30 A, T _J =25°C	---	0.82	1.5	V

Note :

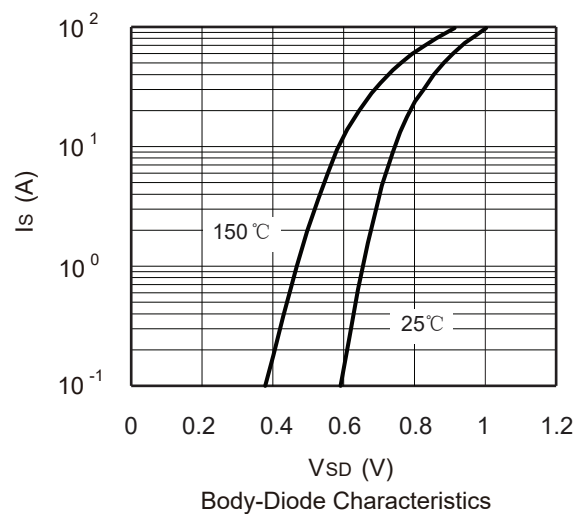
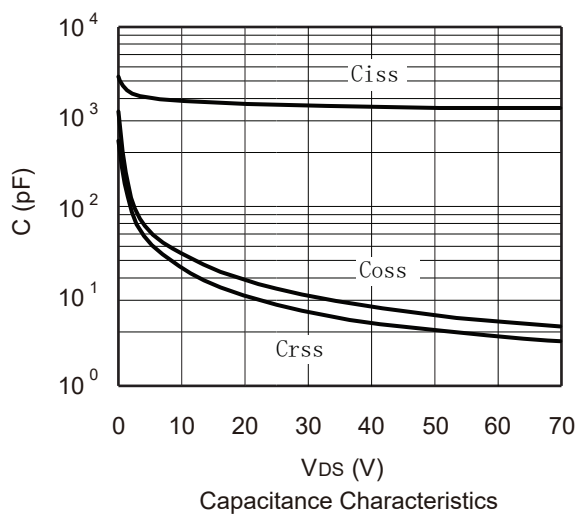
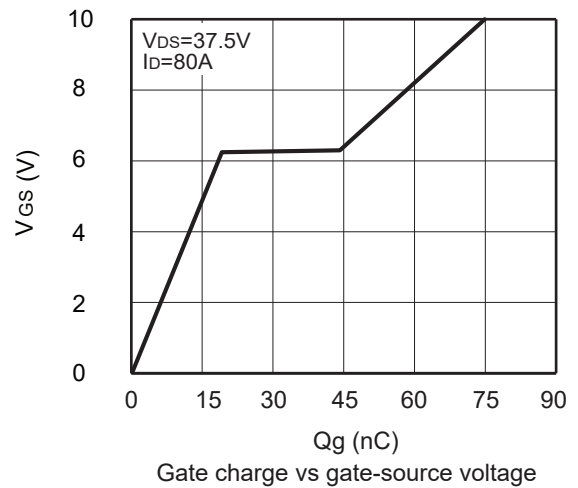
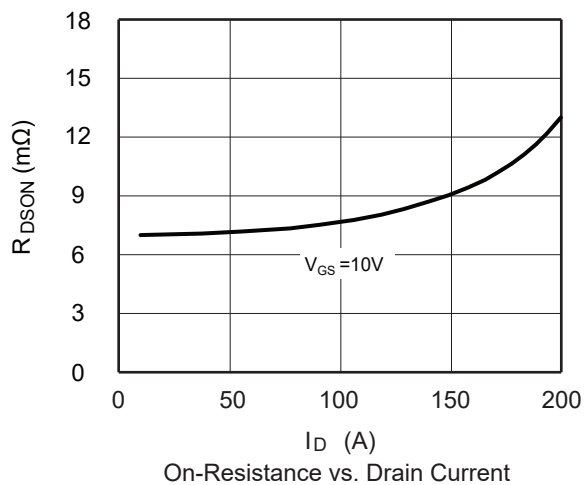
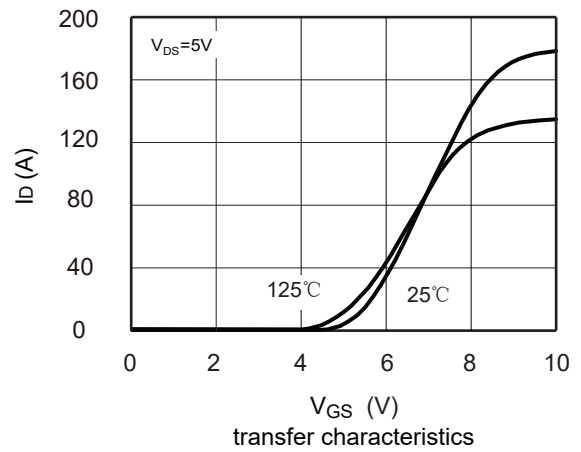
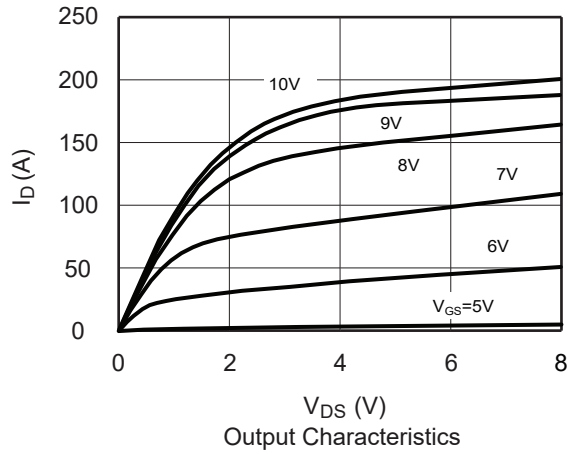
- 1.Pulse width limited by safe operating area
- 2.Starting T_J=25 °C, I_D=40 A, V_{DD}= 34 V
- 3.Pulsed: pulse duration=300μs, duty cycle 1.5%

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

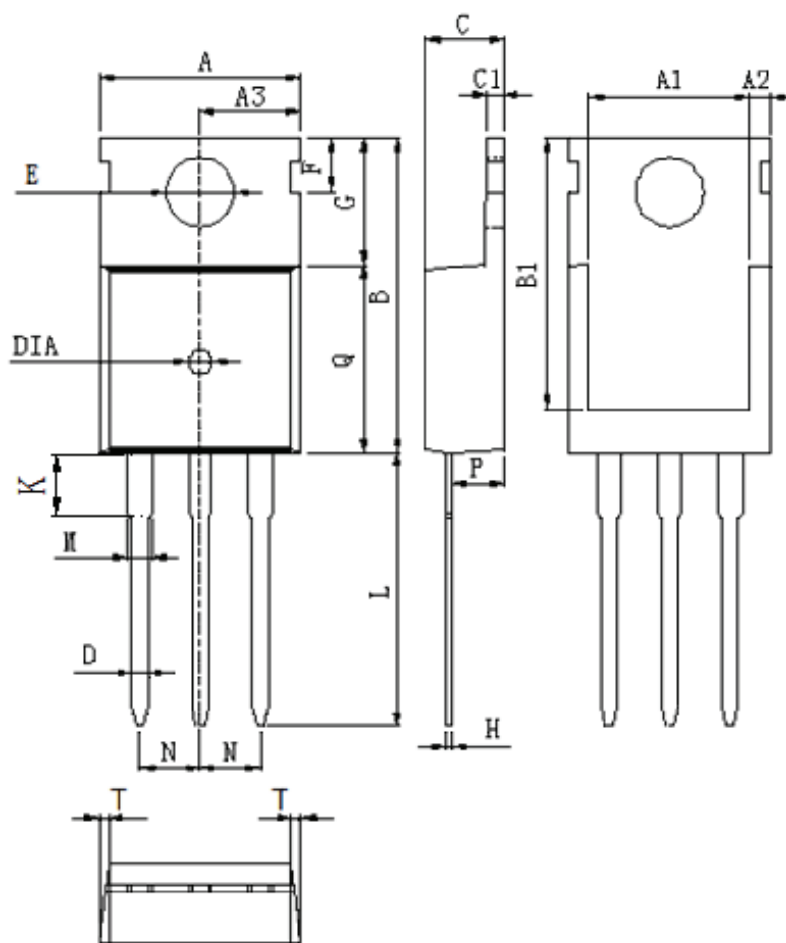
Typical Characteristics



Package Dimension

TO-220

Unit :mm

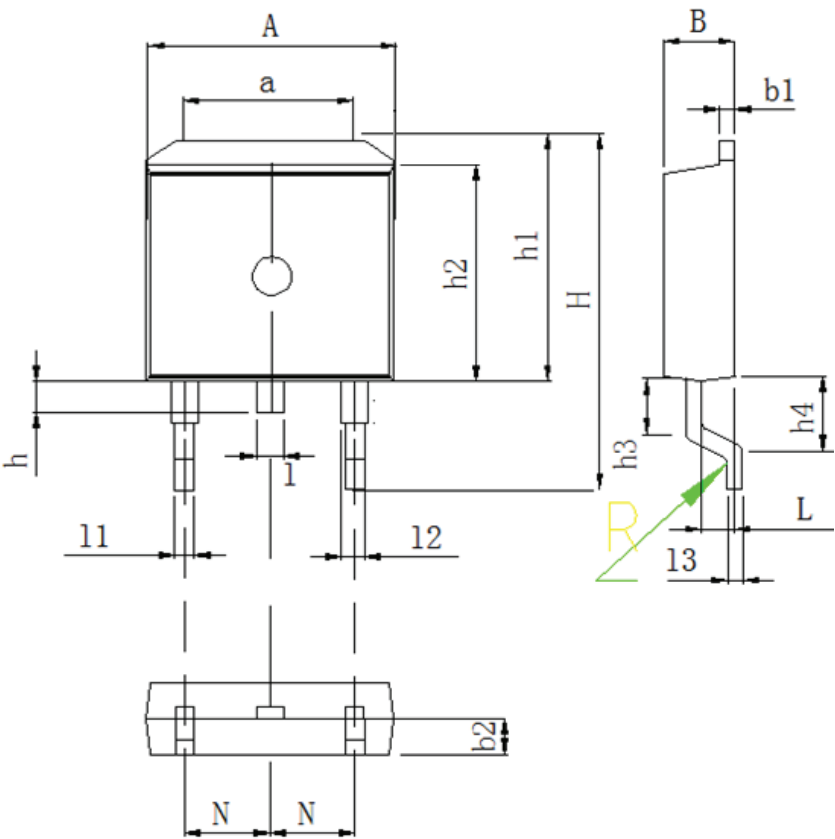


DIM	MILLIMETERS
A	10.0 ± 0.3
A1	8.64 ± 0.2
A2	1.15 ± 0.1
A3	5.0 ± 0.2
B	15.8 ± 0.4
B1	13.2 ± 0.3
C	4.56 ± 0.1
C1	1.3 ± 0.2
D	0.8 ± 0.2
E	3.6 ± 0.2
F	2.95 ± 0.3
G	6.5 ± 0.3
H	0.5 ± 0.1
K	3.1 ± 0.2
L	13.2 ± 0.4
M	1.25 ± 0.1
N	2.54 ± 0.1
P	2.4 ± 0.3
Q	9.0 ± 0.3
T	W:0.35
DIA	$\odot 1.5$ (deep 0.2)

Package Dimension

TO-263

Unit :mm

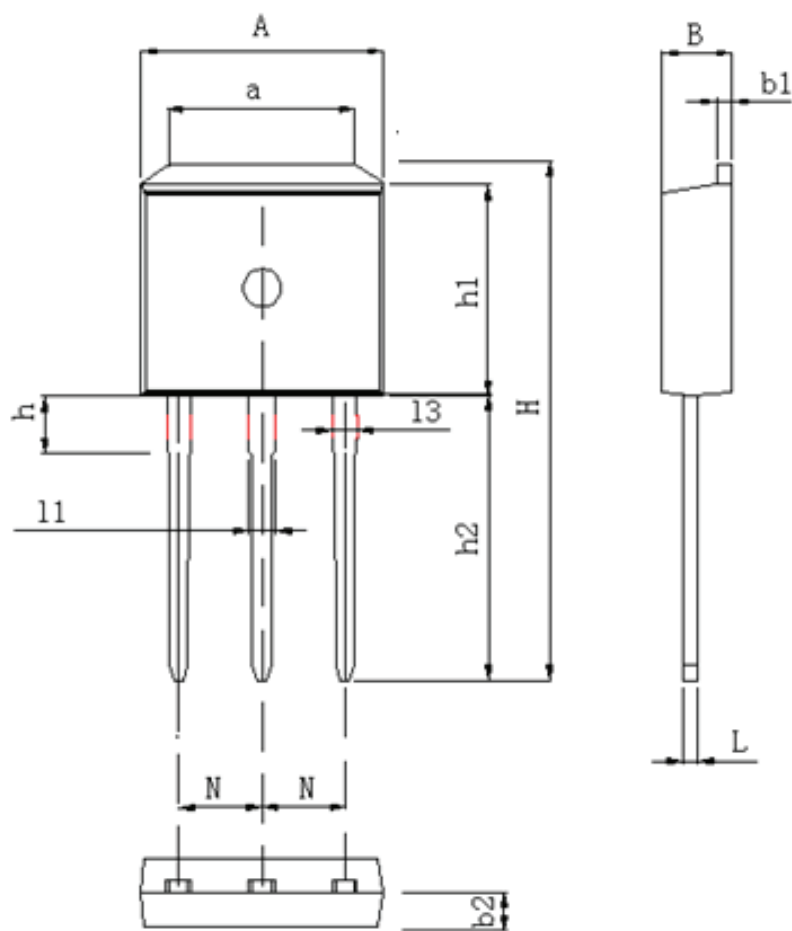


DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

Package Dimension

TO-262

Unit :mm



DIM	MILLIMETERS
A	9.98±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	23.9±0.3
h	3.1±0.2
h1	9.16±0.2
h2	13.2±0.2
L	0.5±0.1
11	1.3±0.1
12	0.8±0.1
N	2.45±0.1